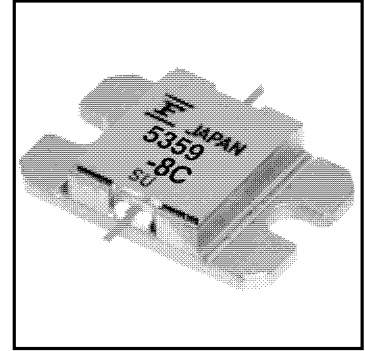


### FEATURES

- High Output Power:  $P_{1dB} = 39dBm$  (Typ.)
- High Gain:  $G_{1dB} = 9.5dB$  (Typ.)
- High PAE:  $\eta_{add} = 32%$  (Typ.)
- Broad Band: 5.3 ~ 5.9GHz
- Impedance Matched  $Z_{in}/Z_{out} = 50\Omega$
- Hermetically Sealed Package



### DESCRIPTION

The FLM5359-8C is a power GaAs FET that is internally matched for standard communication bands to provide optimum power and gain in a 50 ohm system.

Fujitsu's stringent Quality Assurance Program assures the highest reliability and consistent performance.

### ABSOLUTE MAXIMUM RATING (Ambient Temperature $T_a=25^\circ C$ )

Item	Symbol	Condition	Rating	Unit
Drain-Source Voltage	$V_{DS}$		15	V
Gate-Source Voltage	$V_{GS}$		-5	V
Total Power Dissipation	$P_T$	$T_C = 25^\circ C$	42.8	W
Storage Temperature	$T_{stg}$		-65 to +175	$^\circ C$
Channel Temperature	$T_{ch}$		175	$^\circ C$

Fujitsu recommends the following conditions for the reliable operation of GaAs FETs:

1. The drain-source operating voltage ( $V_{DS}$ ) should not exceed 10 volts.
2. The forward and reverse gate currents should not exceed 16.0 and -4.4 mA respectively with gate resistance of 100 $\Omega$ .

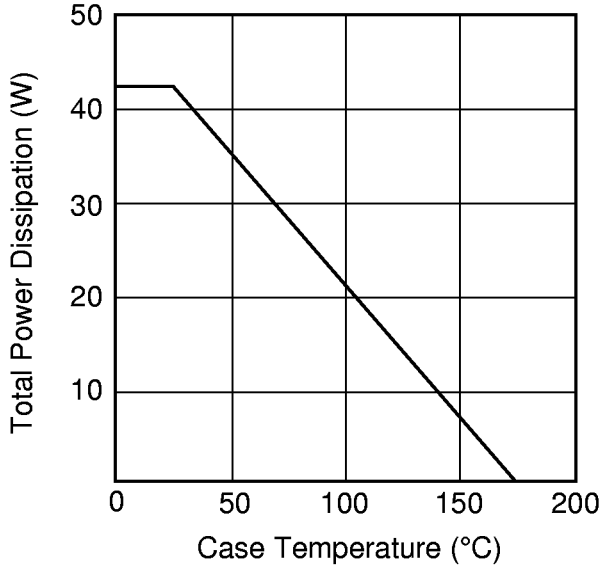
### ELECTRICAL CHARACTERISTICS (Ambient Temperature $T_a=25^\circ C$ )

Item	Symbol	Test Conditions	Limit			Unit
			Min.	Typ.	Max.	
Saturated Drain Current	$I_{DSS}$	$V_{DS} = 5V, V_{GS} = 0V$	-	3600	5400	mA
Transconductance	$g_m$	$V_{DS} = 5V, I_{DS} = 2200mA$	-	2000	-	mS
Pinch-off Voltage	$V_p$	$V_{DS} = 5V, I_{DS} = 180mA$	-1.0	-2.0	-3.5	V
Gate Source Breakdown Voltage	$V_{GSO}$	$I_{GS} = -180\mu A$	-5	-	-	V
Output Power at 1dB G.C.P.	$P_{1dB}$	$V_{DS} = 10V$ $I_{DS} \approx 0.6 I_{DSS}$ (Typ.), $f = 5.3 \sim 5.9$ GHz, $Z_S = Z_L = 50$ ohm	38	39	-	dBm
Power Gain at 1dB G.C.P.	$G_{1dB}$		8.5	9.5	-	dB
Drain Current	$I_{dsr}$		-	2200	2600	mA
Power-added Efficiency	$\eta_{add}$		-	32	-	%
Thermal Resistance	$R_{th}$		Channel to Case	-	3	3.5

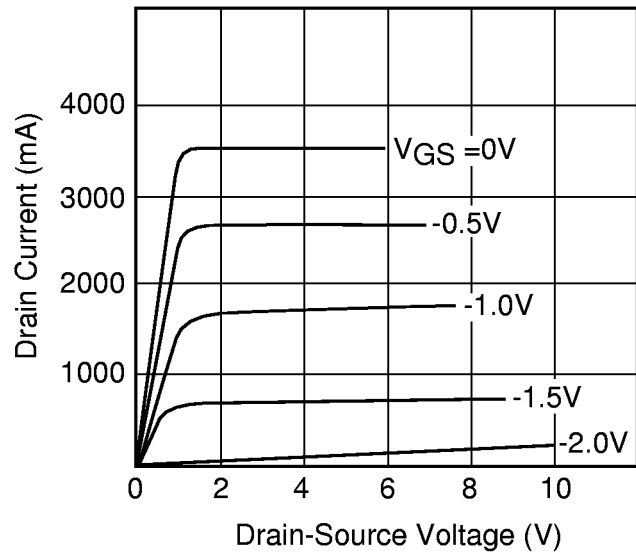
CASE STYLE: IB

G.C.P.: Gain Compression Point

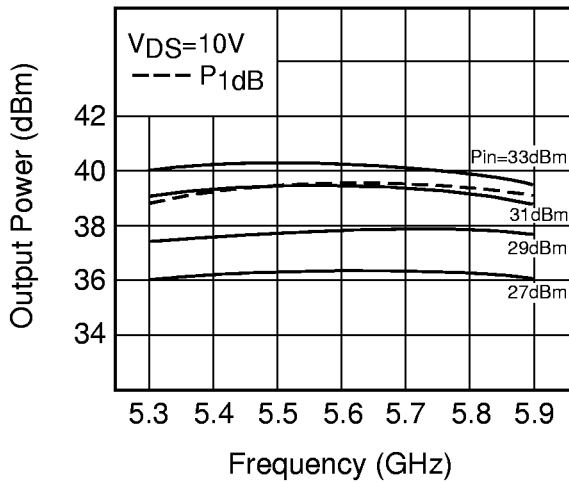
**POWER DERATING CURVE**



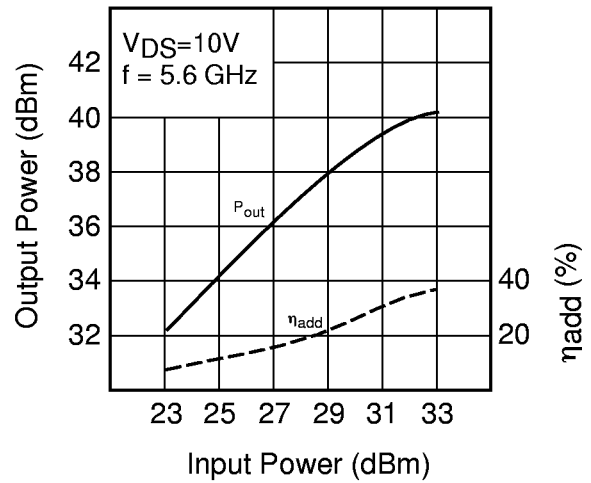
**DRAIN CURRENT vs. DRAIN-SOURCE VOLTAGE**

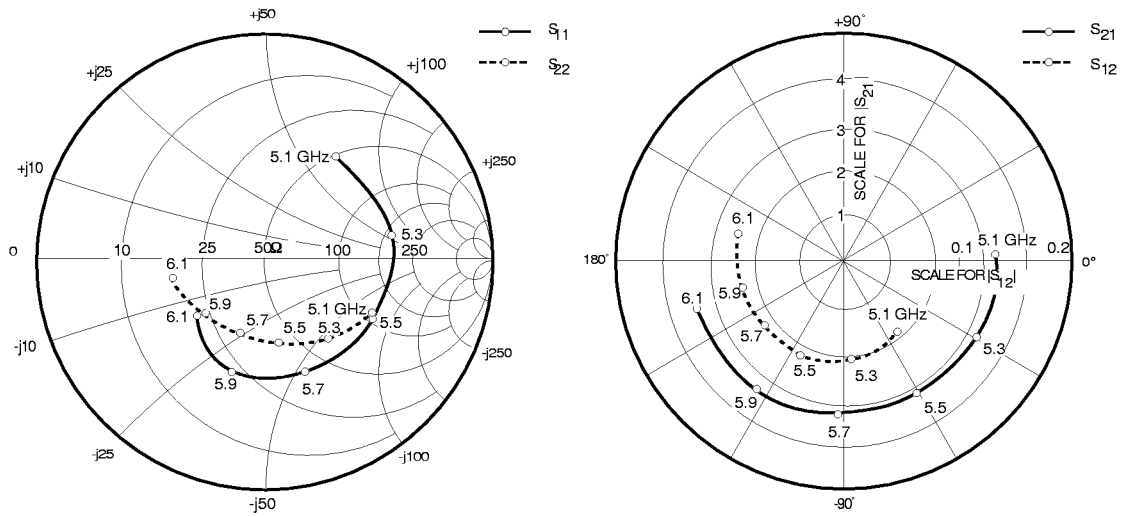


**OUTPUT POWER vs. FREQUENCY**



**OUTPUT POWER vs. INPUT POWER**





### S-PARAMETERS

$V_{DS} = 10V, I_{DS} = 2200mA$

FREQUENCY (MHZ)	S11		S21		S12		S22	
	MAG	ANG	MAG	ANG	MAG	ANG	MAG	ANG
5100	.554	55.1	3.300	2.5	.076	-53.6	.541	-25.3
5200	.566	31.7	3.331	-13.7	.082	-69.4	.496	-37.6
5300	.573	10.8	3.338	-29.9	.085	-85.2	.451	-50.4
5400	.566	-8.6	3.308	-45.8	.087	-100.6	.409	-63.7
5500	.544	-28.0	3.287	-61.6	.089	-115.5	.374	-77.2
5600	.528	-47.6	3.283	-76.9	.088	-128.1	.345	-90.7
5700	.526	-67.3	3.305	-92.3	.088	-140.8	.332	-104.1
5800	.526	-85.7	3.338	-108.2	.090	-152.4	.330	-118.8
5900	.505	-102.9	3.367	-124.9	.092	-166.0	.344	-134.7
6000	.458	-120.0	3.401	-142.5	.094	179.9	.367	-150.5
6100	.380	-138.0	3.435	-160.7	.095	165.5	.397	-167.7

**Case Style "IB"**  
Metal-Ceramic Hermetic Package

